AMENDMENTS TO THE SPECIFICATION

Please replace the current title with the following new title:

-- BURIED CONDUCTOR PATTERNS FORMED BY SURFACE TRANSFORMATION OF EMPTY SPACES IN SOLID STATE MATERIALS --.

Please amend the paragraph on page 19 starting at line 10, as follows:

In addition, further steps to create a functional memory cell on the silicon substrate 10 may be carried out. Thus, additional multilevel interconnect layers and associated dielectric layers could be formed to create operative electrical paths from the buried silicon structure 100 to a source/drain region (not shown) adjacent to a transistor gate structure (not shown) of the substrate 10, or to any active devices 102, 104, 106 (Figure 14) which will be eventually fabricated over the substrate 10. The substrate containing the buried conductors can be used in the formation of many types of integrated circuits such as memories, for example, DRAMs, processors etc.